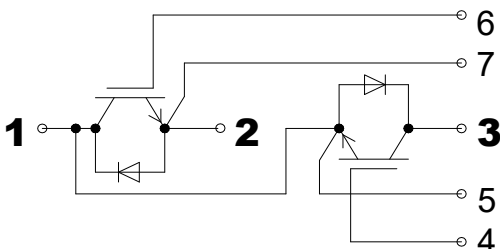


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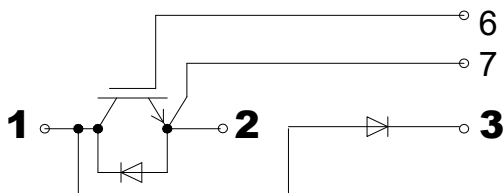
Ultra Fast IGBT Modules



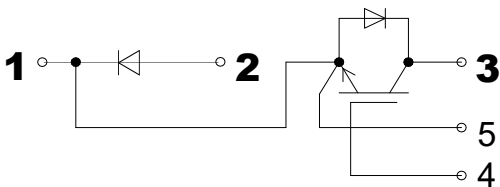
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SGD150N125UC2



SDG150N125UC2



Symbol	Test Condition	Value	Unit
IGBT			
V_{CES}		1200	V
I_C	$T_C = 25(100)^{\circ}\text{C}$ per chip	150(100)	A
V_{GES}		± 20	V
T_{vj} (T_{stg})		$-40 \sim +150(125)$	$^{\circ}\text{C}$
P_{tot}		450	W
INVERSE DIODE			
I_F	$T_C = 25(100)^{\circ}\text{C}$ per chip	150(100)	A
I_{FM}		200	A
V_{RRM}		1200	V
I^2t	$T_J = 125^{\circ}\text{C}$, $t = 10\text{ms}$, $V_R = 0\text{V}$	2000	A^2s

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Symbol	Test Conditions	Min	Typ	Max	Unit
IGBT Tc = 25°C unless otherwise specified					
V _{GE(th)}	V _{GE} =V _{CE} , I _C =2mA	4.5	5.5	6.5	V
I _{CES}	V _{GE} =0; V _{CE} =V _{CES} ; T _j =25(125)°C		0.15	0.5	mA
V _{CE(TO)}	T _j =25(125)°C		1.4(1.6)	1.6(1.8)	V
r _{CE}	V _{GE} =15V		11(15)	14(19)	mΩ
V _{CE(sat)}	I _C =100A; V _{GE} =15V; chip level		3.3	3.7	V
C _{ies}	V _{GE} =0V, V _{CE} =25V, f=1MHz		6.0		nF
C _{oes}			0.80		
C _{res}			0.40		
LCE				30	nH
RCC'+EE'	Termial to Case, Tc=25°C		0.35		mΩ
t _{d(on)}	V _{CC} = 600V, I _C = 100A R _{GON} = R _{GOFF} = 10Ω T _j =125°C V _{GE} =±15V		25		ns
t _r			50		ns
t _{d(off)}			290		ns
t _f			90		ns
E _{on} /E _{off}			4.50/2.30		mJ
INVERSE DIODE Tc = 25°C unless otherwise specified					
V _F	I _F =100A; V _{GE} =0V; T _j = 25°C		1.9	2.2	V
Q _{rr}	I _F =100A; V _R =300V; T _j =25°C di/dt = 600A/us, V _{GE} =-15V		8.5		μC
I _{RRM}			75		A
E _{rec}			2.30		mJ
THERMAL CHARACTERISTICS					
R _{th(j-c)}	per IGBT			0.31	K/W
R _{th(j-c)D}	per FRD			0.45	K/W
Mechanical Data					
Ms		2.5		4	Nm
Weight			158		g

Features

- NPT Technology IGBT
- Fast Recovery Free Wheeling Diode
- Low Switching Losses
- $V_{ce(sat)}$ with positive temperature coefficient
- Fast Switching and short tail current
- Switched mode power supplies at $f_{sw}>20KHz$
- Resonant inverters up to 100KHz
- Electronic Welders at $f_{sw}>20KHz$

Application

- Welding inverters
- Inductive Heating

Advantages

- Space and weight savings
- Reduced protection circuits

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Ultra Fast IGBT Modules

Fig 1. output characteristic IGBT,
 $I_c=f(V_{CE}), V_{GE}=15V$

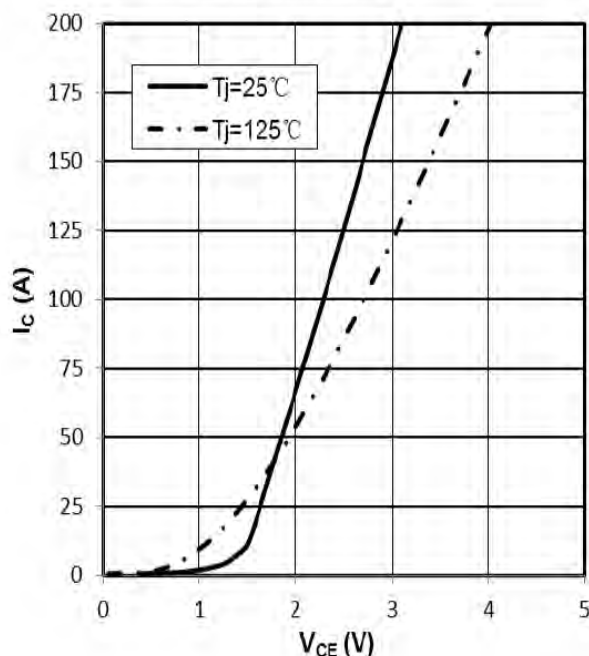


Fig 2. output characteristic IGBT,
 $I_c=f(V_{CE}), T_j=125^\circ\text{C}$

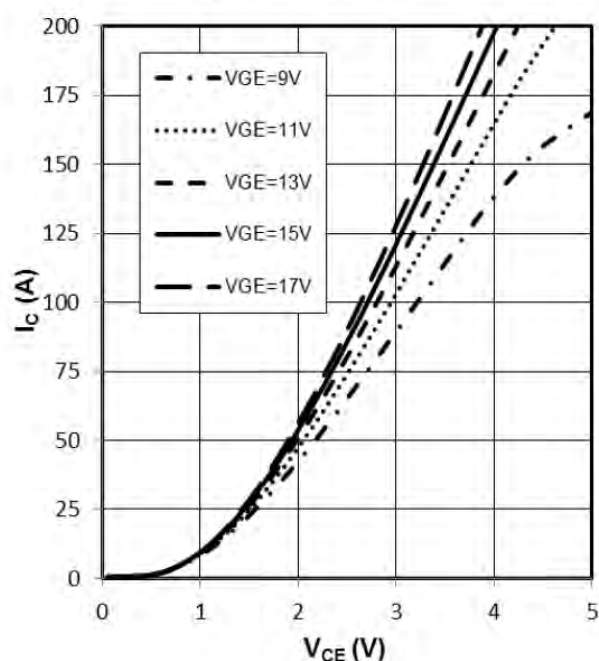


Fig 3. transfer characteristic IGBT,
 $I_c=f(V_{GE}), V_{CE}=20V$

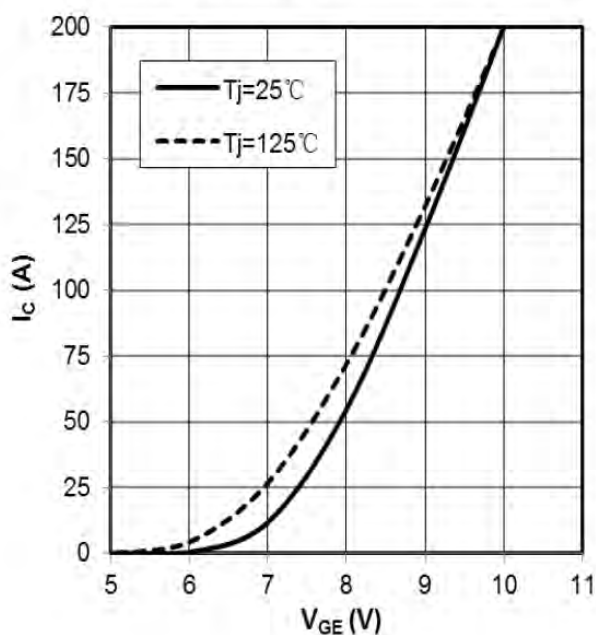
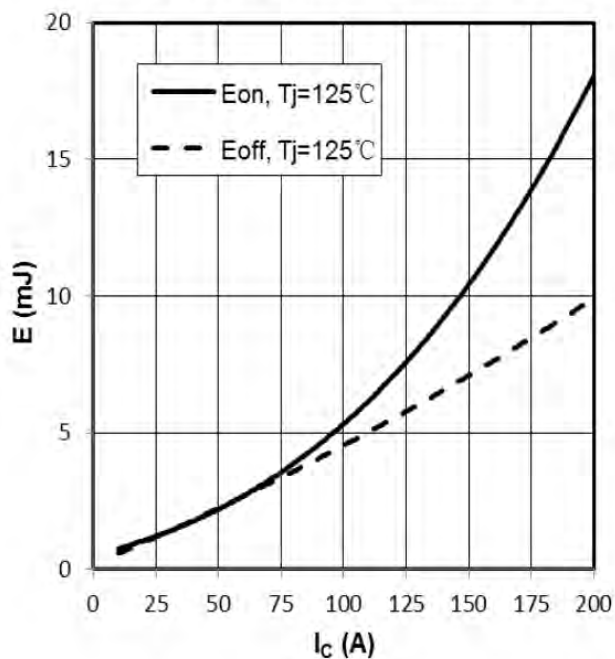


Fig 4. switching losses IGBT, $E_{on}=f(I_c), E_{off}=f(I_c)$,
 $V_{GE}=\pm 15V, R_{Gon}=5.6\Omega, R_{Goff}=5.6\Omega, V_{CE}=600V$



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Fig 5. switching losses IGBT,
 $E_{on}=f(R_g), E_{off}=f(R_g), V_{GE}=\pm 15V, I_C=100A, V_{CE}=600V$

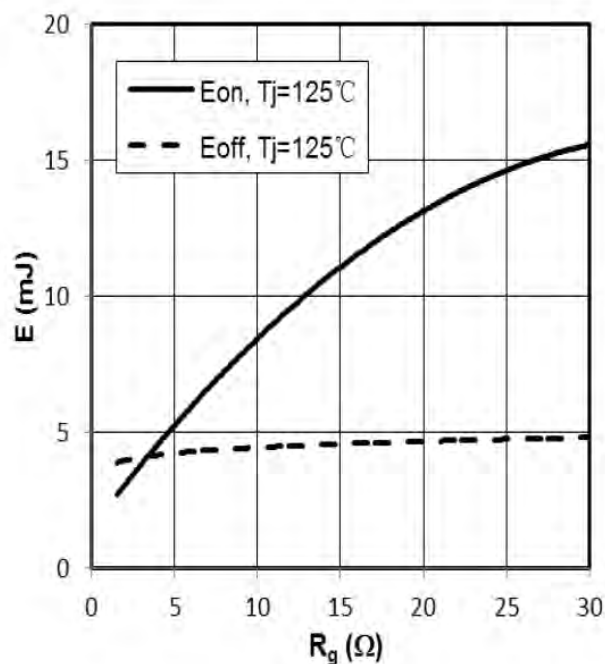


Fig 6. transient thermal impedance IGBT, $Z_{thjc}=f(t)$

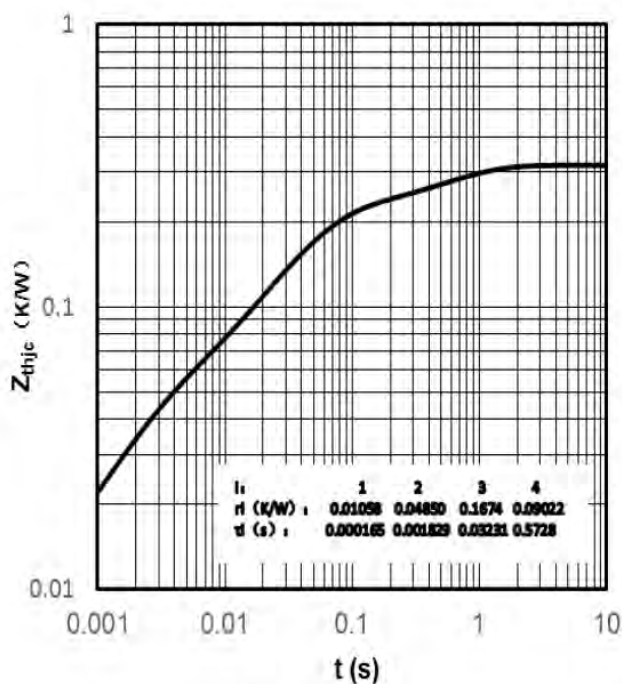


Fig 7. reverse bias safe operating area IGBT,
 $I_C=f(V_{CE}), V_{GE}=\pm 15V, R_{goff}=5.6\Omega, T_{vj}=125^\circ C$

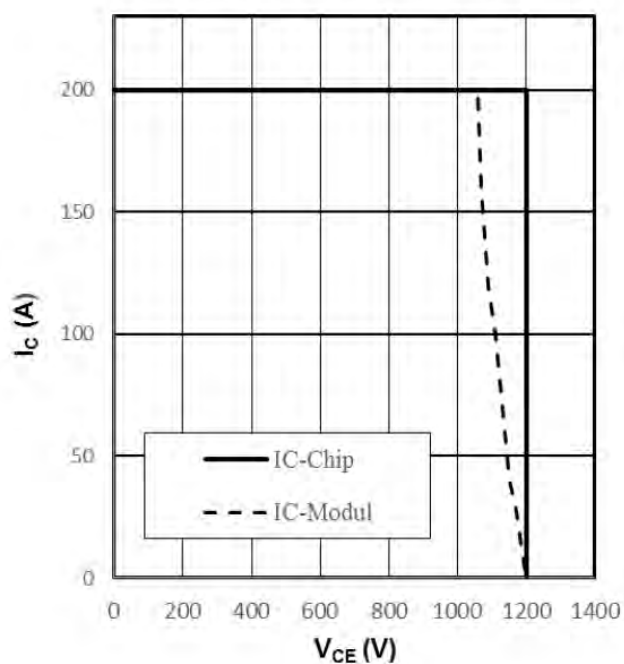
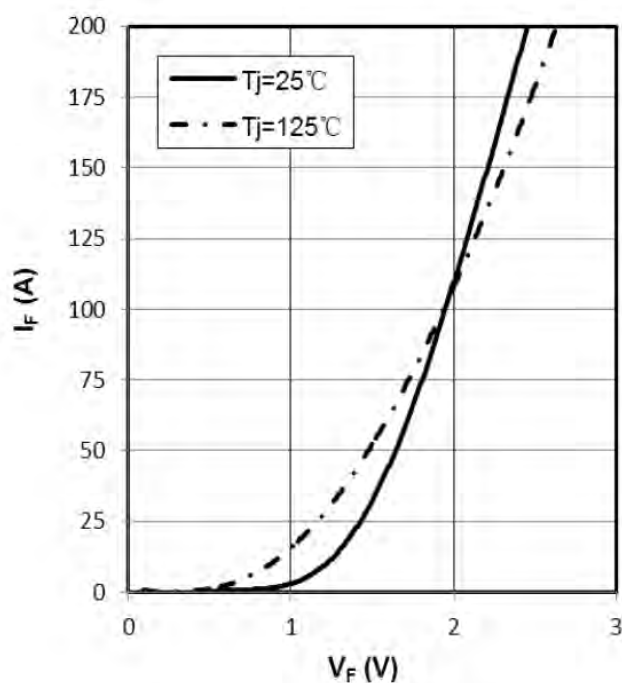


Fig 8. forward characteristic of Diode, $I_F=f(V_F)$



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Fig 9. switching losses Diode,
 $E_{rr}=f(I_F), R_{Gon}=7.5\Omega, V_{CE}=600V$

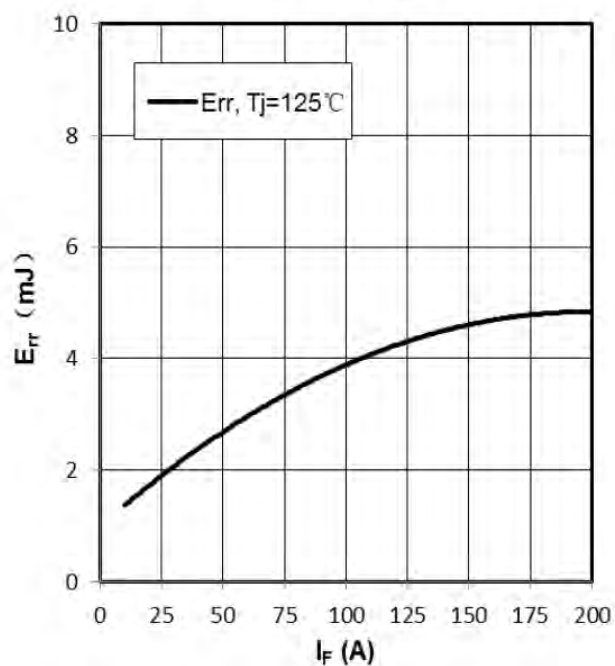
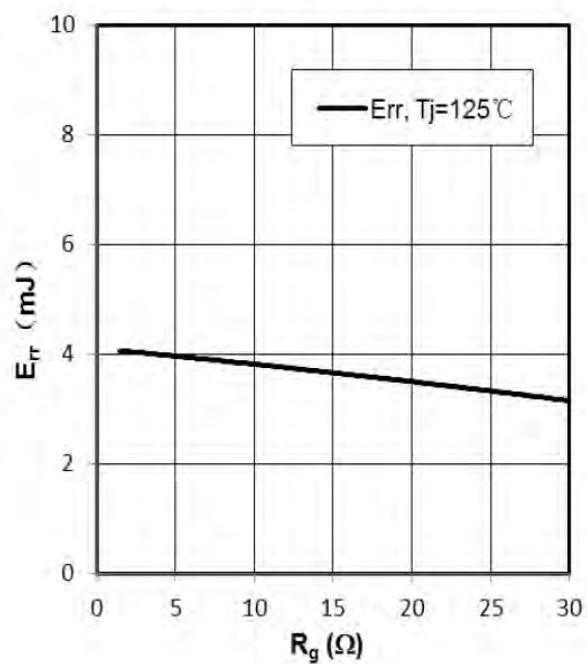


Fig 10. switching losses Diode,
 $E_{rr}=f(R_g), I_F=100A, V_{CE}=600V$



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